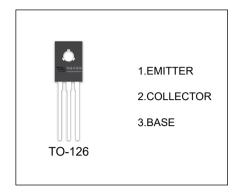


2SC1162 TRANSISTOR (NPN)

FEATURES

Low Frequency Power Amplifier



ORDERING INFORMATION

Part Number	Package	Packing Method	Pack Quantity
2SC1162	TO-126	Bulk	200pcs/Bag
2SC1162-TU	TO-126	Tube	60pcs/Tube

MAXIMUM RATINGS (Ta=25°C unless otherwise noted)

Symbol	Parameter	Value	Unit
V _{CBO}	Collector-Emitter Voltage	35	V
V _{CEO}	Collector-Emitter Voltage	35	V
V _{EBO}	Emitter-Base Voltage	5	V
Ic	Collector Current -Continuous	2.5	Α
Pc	Collector Power Dissipation	1	W
T _J ,T _{stg}	Operation Junction and Storage Temperature Range	-55-150	°C



Parameter	Symbol	Test conditions	Min	Тур	Max	Unit
Collector-base breakdown voltage	V _{(BR)CBO}	I _C =1mA,I _E =0	35			V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C =10mA,I _B =0	35			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E =1mA ,I _C =0	5			V
Collector cut-off current	I _{CBO}	V _{CB} =35V,I _E =0			20	μA
Emitter cut-off current	I _{EBO}	V _{EB} =5V,I _C =0			20	μA
DC aurrent gain	h _{FE1} *	V _{CE} =2V,I _C =0.5A	60		320	
DC current gain	h _{FE2} *	V _{CE} =2V,I _C =1.5A	20			
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =2A,I _B =200mA			1	V
Base-collector voltage	V _{BE}	V _{CE} =2V,I _C =1.5A			1.5	V
Transition frequency	f _T V _{CE} =2V,I _C =200mA			180		MHz

[∗]pulse test

CLASSIFICATION OF h_{FE1}

Rank	В	С	D
Range	60-120	100-200	160-320